Unit in mm

TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL TYPE (PCT PROCESS)

2 S C 2 1 2 0

AUDIO POWER AMPLIFIER APPLICATIONS

• High h_{FE} : $h_{FE(1)} = 100 \sim 320$

• 1 Watts Amplifier Applications.

• Complementary to 2SA950

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	35	V
Collector-Emitter Voltage	v_{CEO}	30	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	800	mA
Base Current	$I_{\mathbf{B}}$	160	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	600	mW
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

1. EMITTER 2. COLLECTOR 3. BASE JEDEC TO-92 EIAJ SC-43

2-5F1B

Weight: 0.21g

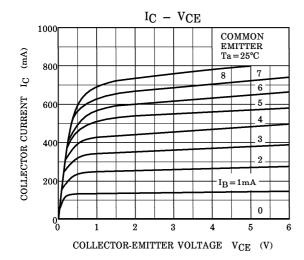
TOSHIBA

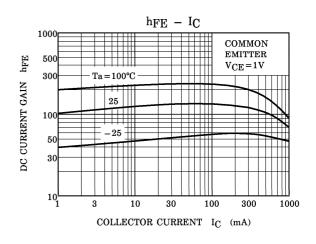
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

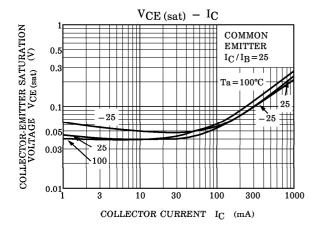
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = 35V, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	_	_	0.1	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C =10mA, I _B =0	30	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{CE} = 1V, I_{C} = 100 \text{mA}$	100	_	320	
	h _{FE} (2)	$V_{CE} = 1V, I_{C} = 700 \text{mA}$	35	_	_	
Collector-Emitter Breakdown Voltage	V _{CE} (sat)	$I_{C} = 500 \text{mA}, I_{B} = 20 \text{mA}$	_	_	0.5	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE}=1V, I_{C}=10mA$	0.5	_	0.8	V
Transition Frequency	$ m f_{T}$	$V_{\text{CE}} = 5V, I_{\text{C}} = 10\text{mA}$	_	120	_	MHz
Collector Output Capacitance	Cob	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	13	_	pF

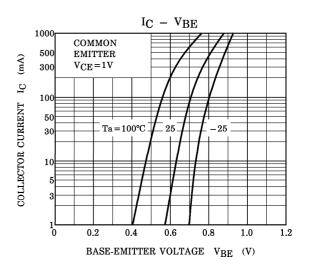
Note: h_{FE} (1) Classification O: $100\sim200$, Y: $160\sim3200$

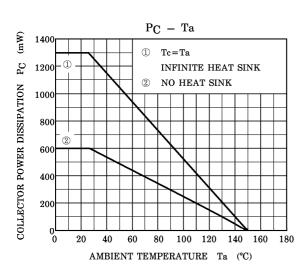
1 2001-05-31











2 2001-05-31

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